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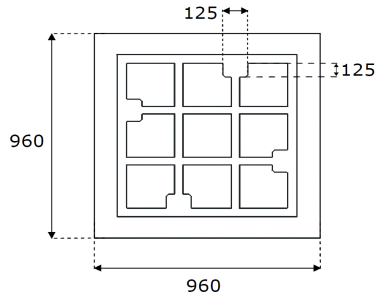
Data Sheet

LED Chip Infrared EOLC-850-11

Rev. 04, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	P (anode) up



typ. dimension (µm)

typ. thickness 160 ± 25 µm

anode - gold alloy, 1.5 µm

cathode - gold alloy, 0.5 µm
structured, 25% covered

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=100 mA	V_F		1.35		V
Forward voltage	I_F=350 mA	V_F		1.7	1.9	V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power*	I_F=20 mA	Φ_e		4		mW
Radiant power*	I_F=350 mA	Φ_e		60		mW
Peak wavelength	I_F=350 mA	λ_p	840	850	860	nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		45		nm
Switching time	I_F=20 mA	t_r, t_f		15; 20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 094

RoHS COMPLIANT Pb-Free